Preliminary datasheet
EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / NTC

Features



- Electrical features
  - V_{DSS} = 2300 V
  - I_{DN} = 120 A / I_{DRM} = 240 A
  - High current density
  - Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder
  - Silicon carbide MOSFET with .XT
- Mechanical features
  - AlN substrate with low thermal resistance
  - High creepage and clearance distances
  - Integrated NTC temperature sensor
  - PressFIT contact technology
  - High power cycling capability due to .XT
  - Pre-applied thermal interface material

Potential applications

- Three-level applications
- Solar applications
- Energy storage systems
- EV charging

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

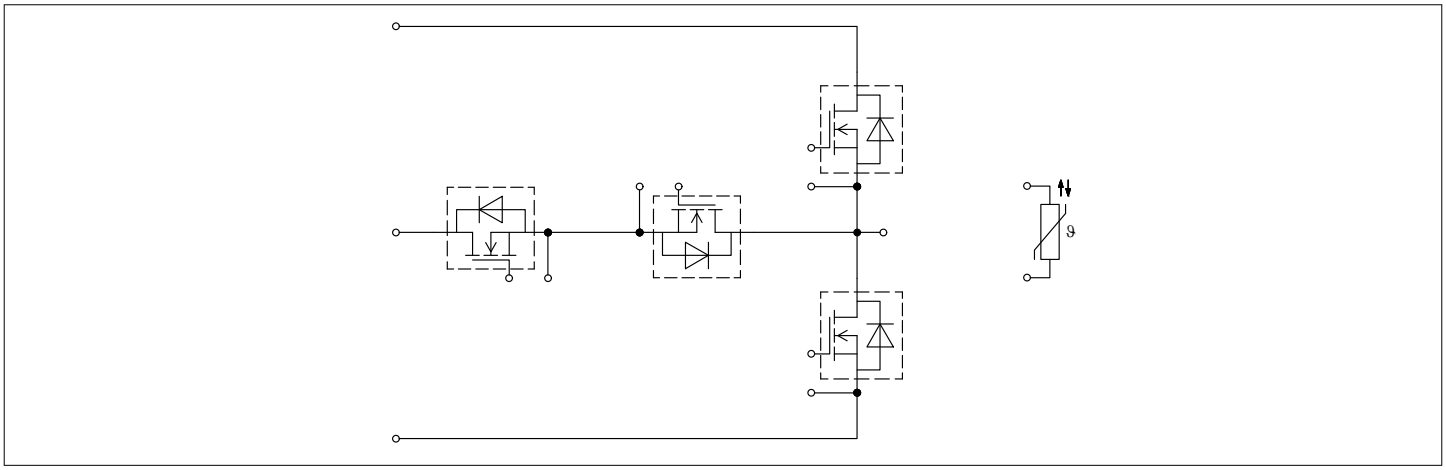


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	3.2	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, f = 50 Hz, *t* = 1 min	3.2	kV
Internal isolation		basic insulation (class 1, IEC 61140)	AlN	
Comparative tracking index	*CTI*		> 600	
Relative thermal index (electrical)	*RTI*	frame	180	°C
		lid	150	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sDS}			22		nH
Module lead resistance, terminals - chip	$R_{DD'+SS'}$	T_H = 25 °C, per switch		2.5		mΩ
Storage temperature	T_{stg}		-40		150	°C
Mounting force per clamp	*F*		40		80	N
Weight	*G*			38		g

***Note**: The current up to 50A per pin is limited by the interaction of the pins with the PCB design and cooling conditions.*

Storage and shipment of modules with TIM => see AN 2012-07.

2 MOSFET, T1 / T2

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	2300	V
Implemented drain current	I_{DN}			120	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 125 °C	120	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		240	A
Gate-source voltage, max. transient voltage	V_{GS}	D < 0.01		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 120 A	V_{GS} = 15 V, T_{vj} = 25 °C		6.7		mΩ
			V_{GS} = 18 V, T_{vj} = 25 °C		6.2		
			V_{GS} = 18 V, T_{vj} = 125 °C		12.4		
			V_{GS} = 18 V, T_{vj} = 175 °C		17.2		
Gate threshold voltage	$V_{GS(th)}$	I_D = 112 mA, V_{DS} = V_{GS}, (tested after 1ms pulse at V_{GS} = +20 V), T_{vj} = 25 °C		3.45	4.1	5.15	V
Total gate charge	Q_G	V_{DD} = 1500 V, V_{GS} = -4/18 V, T_{vj} = 25 °C			0.752		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			1.2		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 1500 V, V_{GS} = 0 V	T_{vj} = 25 °C		21.6		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 1500 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.496		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 1500 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.035		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 1500 V, V_{GS} = -4/18 V, T_{vj} = 25 °C			724		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 2300 V, V_{GS} = -4 V	T_{vj} = 25 °C		1.4		µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 120 A, R_{Gon} = 7.4 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 1000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		98		ns
			T_{vj} = 125 °C		92		
			T_{vj} = 175 °C		87		
Rise time (inductive load)	t_r	I_D = 120 A, R_{Gon} = 7.4 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 1000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		42		ns
			T_{vj} = 125 °C		37		
			T_{vj} = 175 °C		37		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\ off}$	I_D = 120 A, R_{Goff} = 0.25 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		50		ns
			T_{vj} = 125 °C		55		
			T_{vj} = 175 °C		58		
Fall time (inductive load)	t_f	I_D = 120 A, R_{Goff} = 0.25 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		16		ns
			T_{vj} = 125 °C		16		
			T_{vj} = 175 °C		17		
Turn-on energy loss per pulse	E_{on}	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, R_{Gon} = 7.4 Ω, di/dt = 4 kA/µs (T_{vj} = 175 °C), t_{dead} = 1000 ns	T_{vj} = 25 °C		5.1		mJ
			T_{vj} = 125 °C		5.1		
			T_{vj} = 175 °C		5.6		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, $R_{Gon,o}$ = 6.8 Ω, di/dt = 4.2 kA/µs (T_{vj} = 175 °C), t_{dead} = 100 ns	T_{vj} = 25 °C		4.5		mJ
			T_{vj} = 125 °C		4.2		
			T_{vj} = 175 °C		4.3		
Turn-off energy loss per pulse	E_{off}	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, R_{Goff} = 0.25 Ω, dv/dt = 56 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.52		mJ
			T_{vj} = 125 °C		0.54		
			T_{vj} = 175 °C		0.57		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material			0.15		K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		175	°C
Temperature under overload switching conditions	$T_{vj\ over}$	Overload, cumulative max. 200 h				200	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.*

3 Body diode (MOSFET, T1 / T2)

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -4 V	T_H = 90 °C	120	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 120 A, V_{GS} = -4 V	T_{vj} = 25 °C		4		V
			T_{vj} = 125 °C		3.7		
			T_{vj} = 175 °C		3.5		
Peak reverse recovery current	I_{rrm}	I_{SD} = 120 A, di_s/dt = 17.8 kA/µs, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 4000 ns	T_{vj} = 25 °C		220		A
			T_{vj} = 125 °C		285		
			T_{vj} = 175 °C		355		
Recovered charge	Q_{rr}	I_{SD} = 120 A, di_s/dt = 17.8 kA/µs, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 4000 ns	T_{vj} = 25 °C		3.5		µC
			T_{vj} = 125 °C		7.7		
			T_{vj} = 175 °C		12		
Reverse recovery energy	E_{rec}	I_{SD} = 120 A, di_s/dt = 17.8 kA/µs (T_{vj} = 175 °C), V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 4000 ns	T_{vj} = 25 °C		1.5		mJ
			T_{vj} = 125 °C		4.6		
			T_{vj} = 175 °C		7.3		
Reverse recovery energy, optimized	$E_{rec,o}$	I_{SD} = 120 A, di_s/dt = 17.8 kA/µs (T_{vj} = 175 °C), V_{DD} = 750 V, V_{GS} = -4 V, t_{dead} = 400 ns	T_{vj} = 25 °C		1.5		mJ
			T_{vj} = 125 °C		1.8		
			T_{vj} = 175 °C		2.2		

4 MOSFET, T3 / T4

Table 8 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 115 °C	120	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		240	A
Gate-source voltage, max. transient voltage	V_{GS}	D < 0.01		-10/25	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 9 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 120 A	V_{GS} = 15 V, T_{vj} = 25 °C		7.6		mΩ
			V_{GS} = 18 V, T_{vj} = 25 °C		6.3		
			V_{GS} = 18 V, T_{vj} = 125 °C		9.7		
			V_{GS} = 18 V, T_{vj} = 175 °C		12.6		
Gate threshold voltage	$V_{GS(th)}$	I_D = 44 mA, V_{DS} = V_{GS}, (tested after 1ms pulse at V_{GS} = +20 V), T_{vj} = 25 °C		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -4/18 V, T_{vj} = 25 °C			0.326		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			2.6		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		9.6		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.392		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.028		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -4/18 V, T_{vj} = 25 °C			161		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -4 V	T_{vj} = 25 °C		0.4		µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = -4 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 120 A, R_{Gon} = 0.25 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 4000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		22		ns
			T_{vj} = 125 °C		22		
			T_{vj} = 175 °C		22		
Rise time (inductive load)	t_r	I_D = 120 A, R_{Gon} = 0.25 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 4000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		9		ns
			T_{vj} = 125 °C		9		
			T_{vj} = 175 °C		9		
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 120 A, R_{Goff} = 5.1 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		96		ns
			T_{vj} = 125 °C		108		
			T_{vj} = 175 °C		115		
Fall time (inductive load)	t_f	I_D = 120 A, R_{Goff} = 5.1 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		41		ns
			T_{vj} = 125 °C		43		
			T_{vj} = 175 °C		44		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy loss per pulse	E_{on}	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, R_{Gon} = 0.25 Ω, di/dt = 17.8 kA/µs (T_{vj} = 175 °C), t_{dead} = 4000 ns	T_{vj} = 25 °C		0.56		mJ
			T_{vj} = 125 °C		0.53		
			T_{vj} = 175 °C		0.53		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, $R_{Gon,o}$ = 0.25 Ω, di/dt = 17.8 kA/µs (T_{vj} = 175 °C), t_{dead} = 400 ns	T_{vj} = 25 °C		0.56		mJ
			T_{vj} = 125 °C		0.53		
			T_{vj} = 175 °C		0.53		
Turn-off energy loss per pulse	E_{off}	I_D = 120 A, V_{DD} = 750 V, L_σ = 15 nH, V_{GS} = -4/18 V, R_{Goff} = 5.1 Ω, dv/dt = 19.1 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		1.69		mJ
			T_{vj} = 125 °C		1.77		
			T_{vj} = 175 °C		1.85		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material			0.26		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C
Temperature under overload switching conditions	$T_{vj\,over}$	Overload, cumulative max. 200 h				200	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.*

5 Body diode (MOSFET, T3 / T4)

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -4 V	T_H = 25 °C	115	A

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 120 A, V_{GS}=-4 V	T_{vj} = 25 °C		4.6		V
			T_{vj} = 125 °C		4.2		
			T_{vj} = 175 °C		4.1		

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Peak reverse recovery current	I_{rrm}	I_{SD} = 120 A, di_s/dt = 4 kA/µs, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		43		A
			T_{vj} = 125 °C		61		
			T_{vj} = 175 °C		80		
Recovered charge	Q_{rr}	I_{SD} = 120 A, di_s/dt = 4 kA/µs, V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.62		µC
			T_{vj} = 125 °C		1.47		
			T_{vj} = 175 °C		2.3		
Reverse recovery energy	E_{rec}	I_{SD} = 120 A, di_s/dt = 4 kA/µs (T_{vj} = 175 °C), V_{DD} = 750 V, V_{GS} = -4/18 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.07		mJ
			T_{vj} = 125 °C		0.28		
			T_{vj} = 175 °C		0.53		
Reverse recovery energy, optimized	$E_{rec,o}$	I_{SD} = 120 A, di_s/dt = 4.2 kA/µs (T_{vj} = 175 °C), V_{DD} = 750 V, V_{GS} = -4 V, t_{dead} = 100 ns	T_{vj} = 25 °C		0.07		mJ
			T_{vj} = 125 °C		0.16		
			T_{vj} = 175 °C		0.25		

6 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

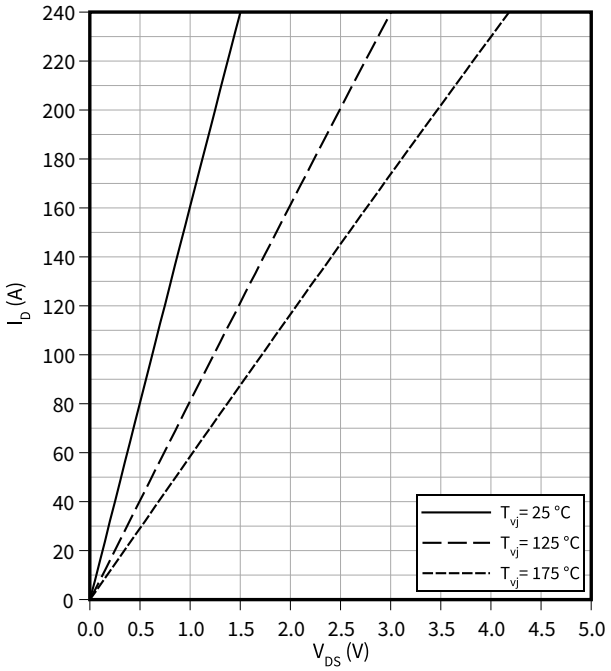
***Note**: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4*

7 Characteristics diagrams

Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

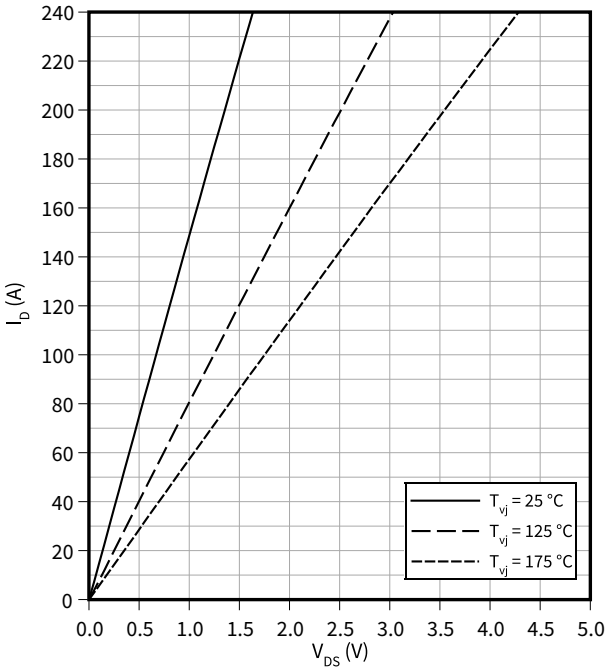
V_{GS} = 18 V



Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

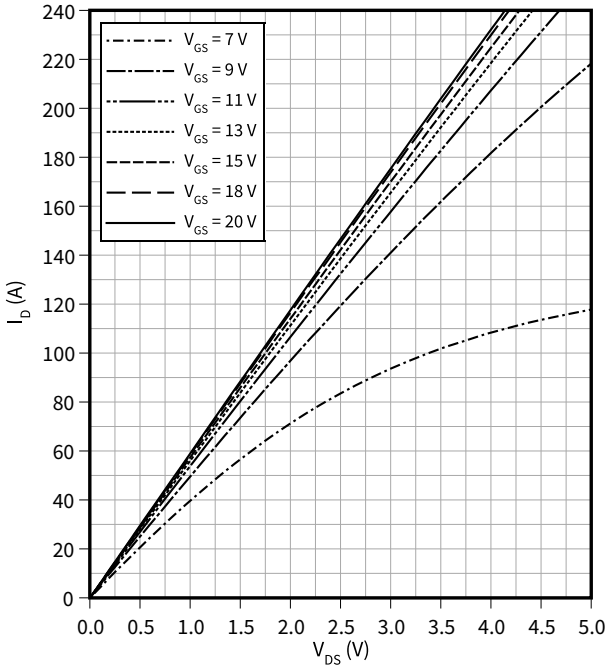
V_{GS} = 15 V



Output characteristic field (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

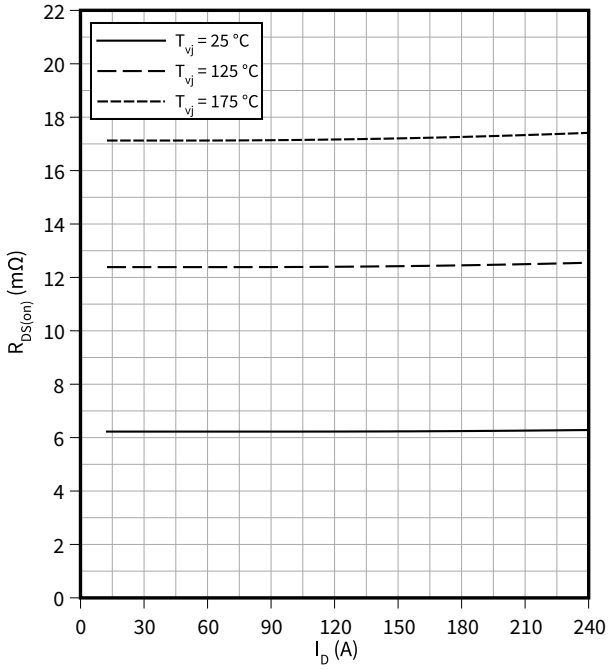
T_{vj} = 175 °C



Drain source on-resistance (typical), MOSFET, T1 / T2

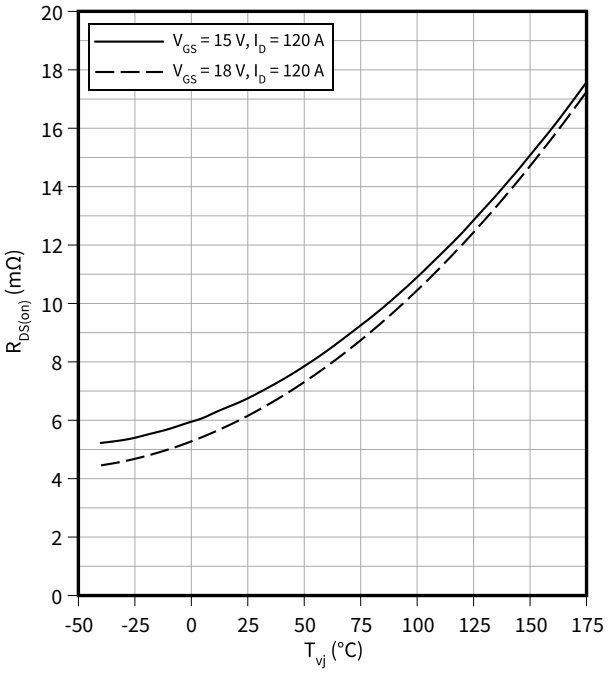
$R_{DS(on)} = f(I_D)$

V_{GS} = 18 V



Drain source on-resistance (typical), MOSFET, T1 / T2

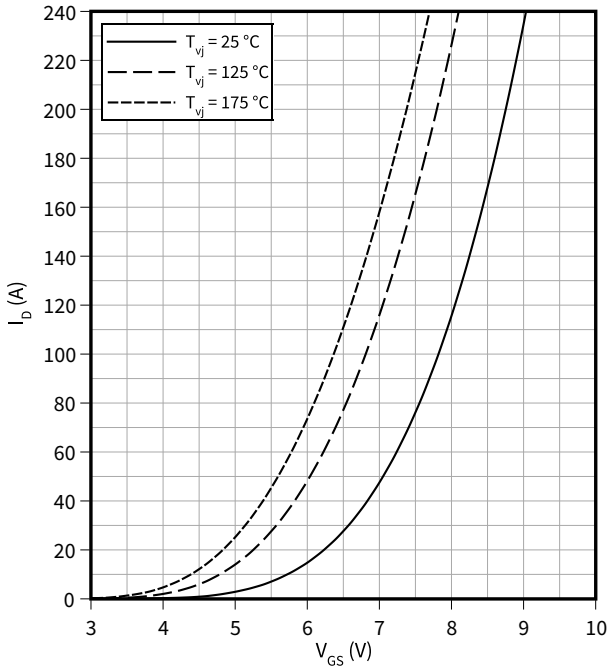
$R_{DS(on)} = f(T_{vj})$



Transfer characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{GS})$

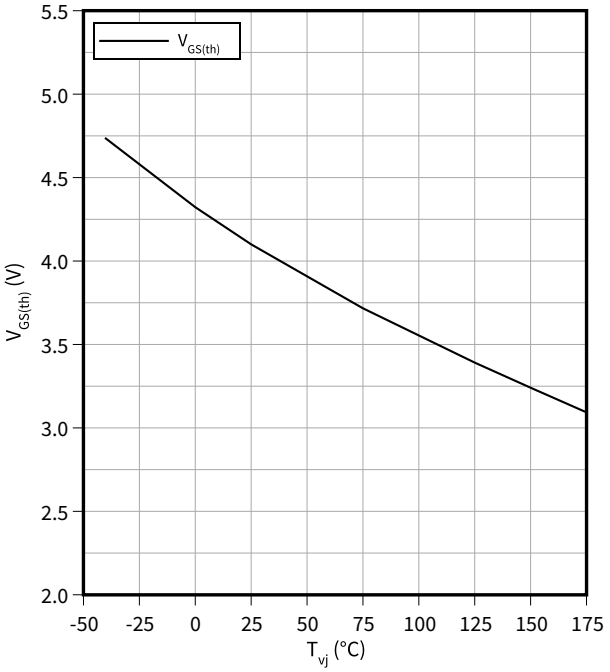
$V_{DS} = 20$ V



Gate-source threshold voltage (typical), MOSFET, T1 / T2

$V_{GS(th)} = f(T_{vj})$

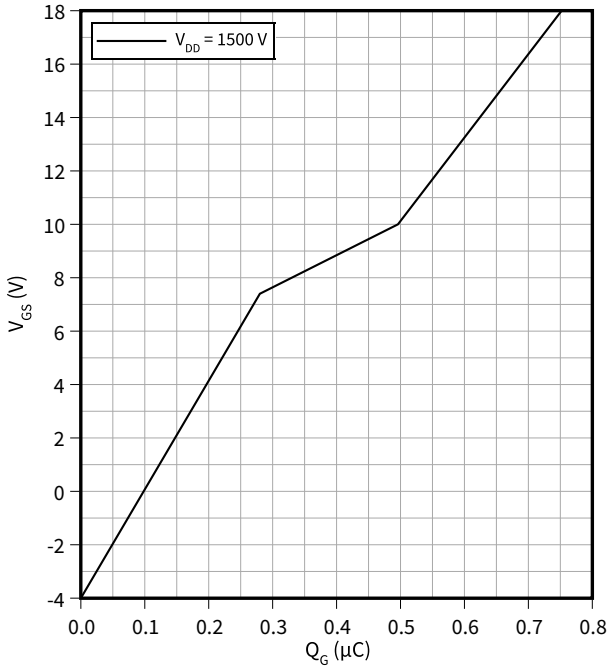
$I_D = 112$ mA, $V_{GS} = V_{DS}$



Gate charge characteristic (typical), MOSFET, T1 / T2

$V_{GS} = f(Q_G)$

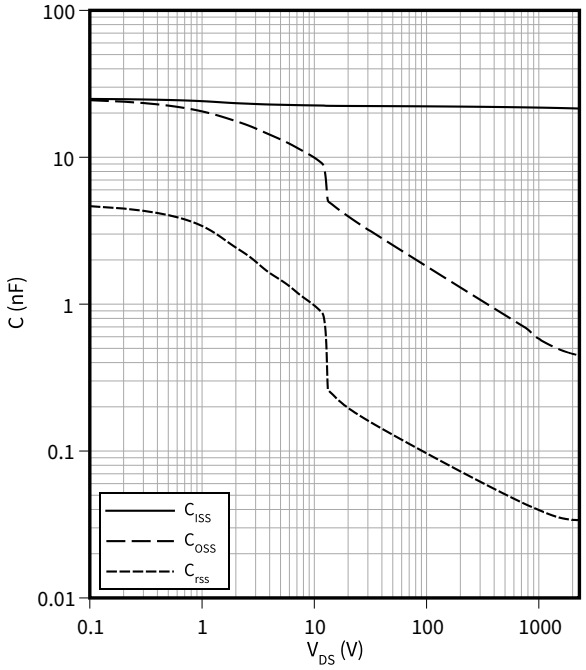
$I_D = 120$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET, T1 / T2

C = f(V_{DS})

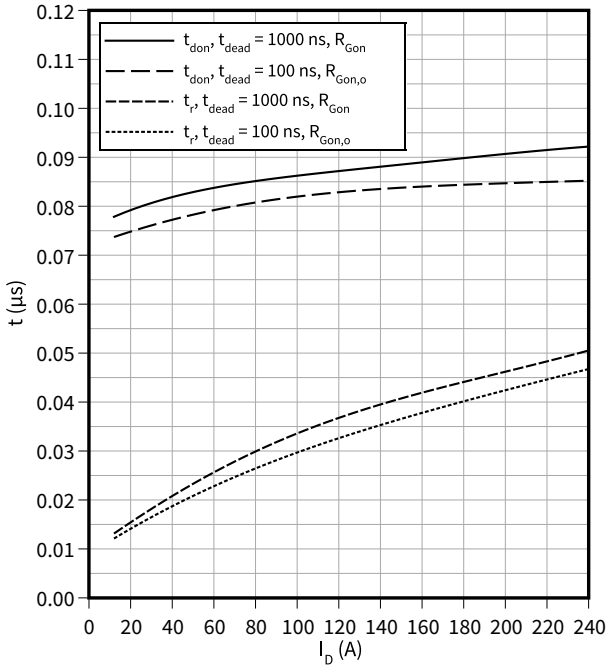
f = 100 kHz, T_{vj} = 25 °C, V_{GS} = 0 V



Switching times (typical), MOSFET, T1 / T2

t = f(I_D)

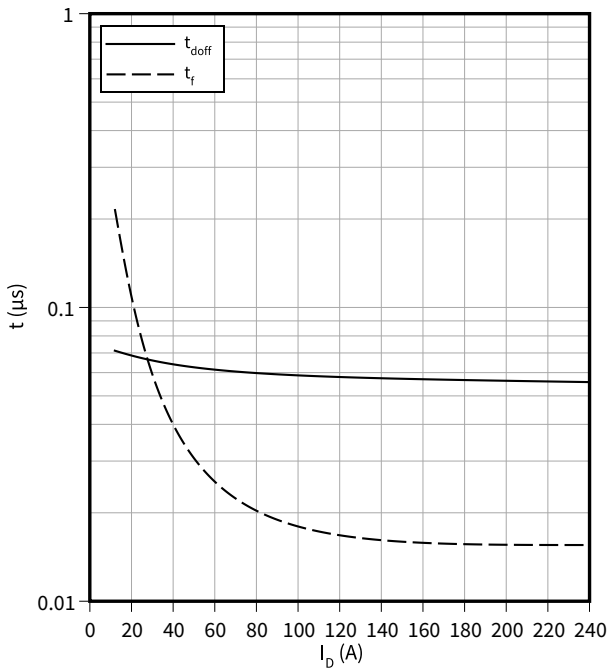
V_{DD} = 750 V, R_{Gon} = 7.4 Ω, $R_{Gon,o}$ = 6.8 Ω, T_{vj} = 175 °C, V_{GS} = -4/18 V



Switching times (typical), MOSFET, T1 / T2

t = f(I_D)

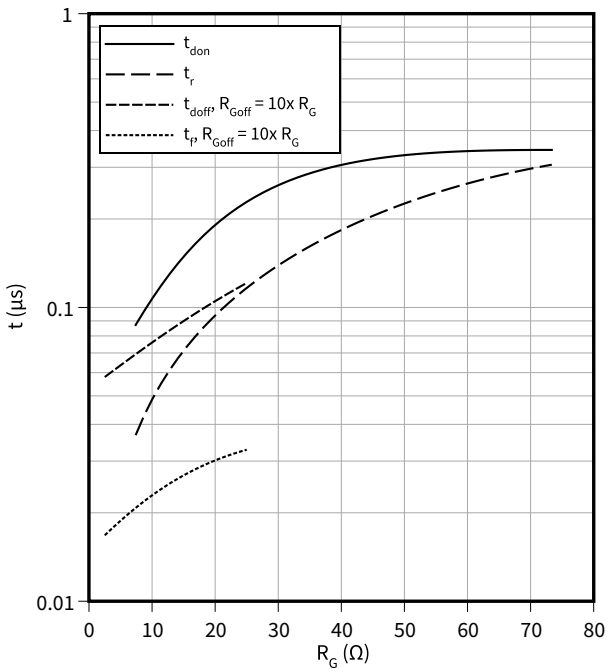
R_{Goff} = 0.25 Ω, V_{DD} = 750 V, T_{vj} = 175 °C, V_{GS} = -4/18 V



Switching times (typical), MOSFET, T1 / T2

t = f(R_G)

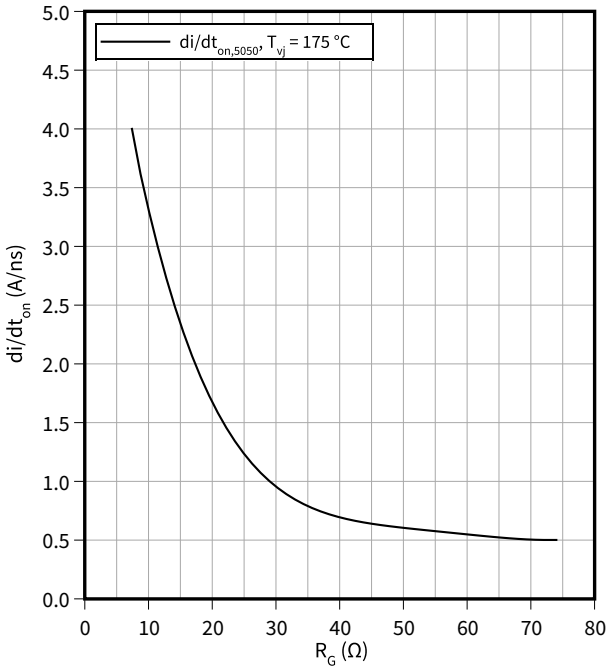
V_{DD} = 750 V, t_{dead} = 1000 ns, I_D = 120 A, T_{vj} = 175 °C, V_{GS} = -4/18 V



Current slope (typical), MOSFET, T1 / T2

$di/dt_{on} = f(R_G)$

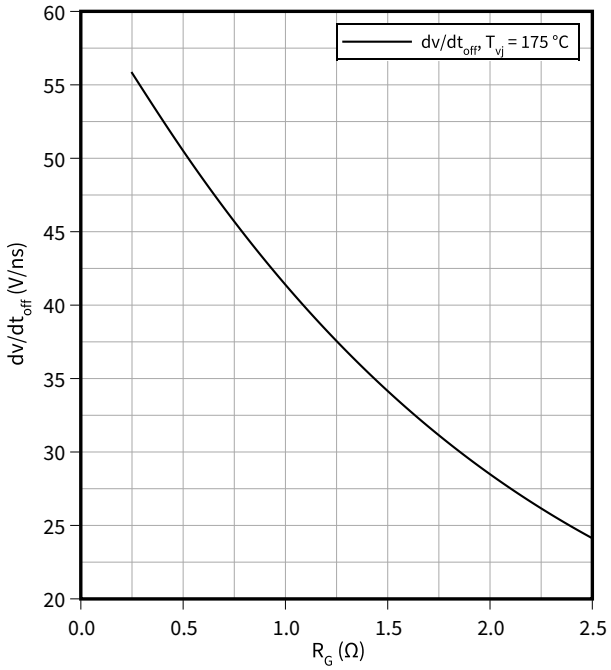
V_{DD} = 750 V, t_{dead} = 1000 ns, I_D = 120 A, V_{GS} = -4/18 V



Voltage slope (typical), MOSFET, T1 / T2

$dv/dt_{off} = f(R_G)$

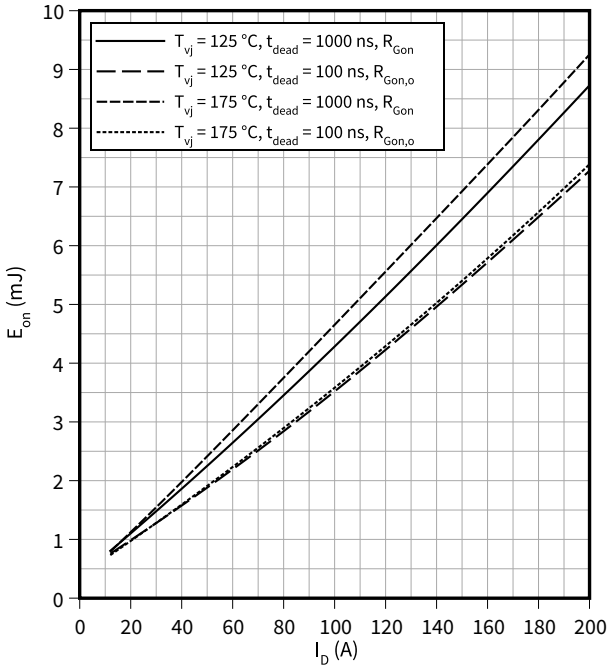
V_{DD} = 750 V, I_D = 120 A, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(I_D)$

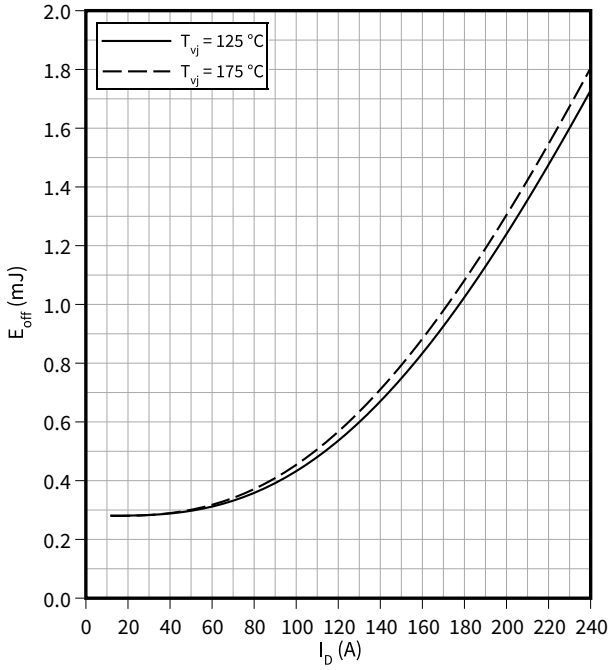
V_{DD} = 750 V, R_{Gon} = 7.4 Ω, $R_{Gon,o}$ = 6.8 Ω, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{off} = f(I_D)$

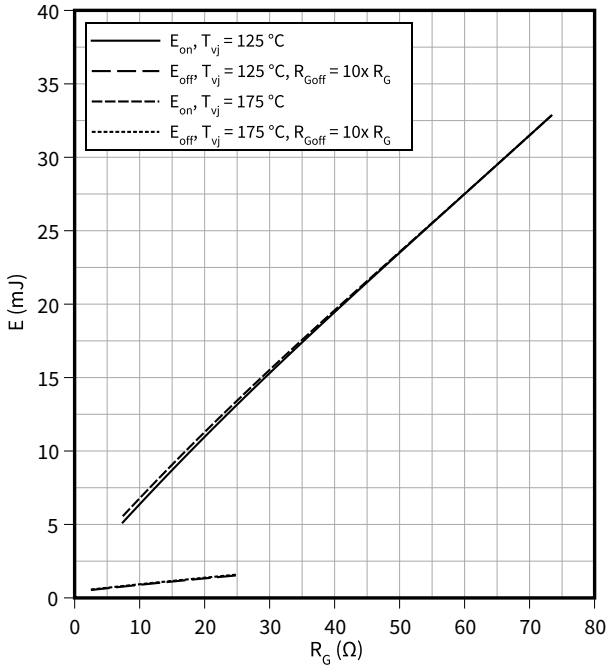
R_{Goff} = 0.25 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T1 / T2

$E = f(R_G)$

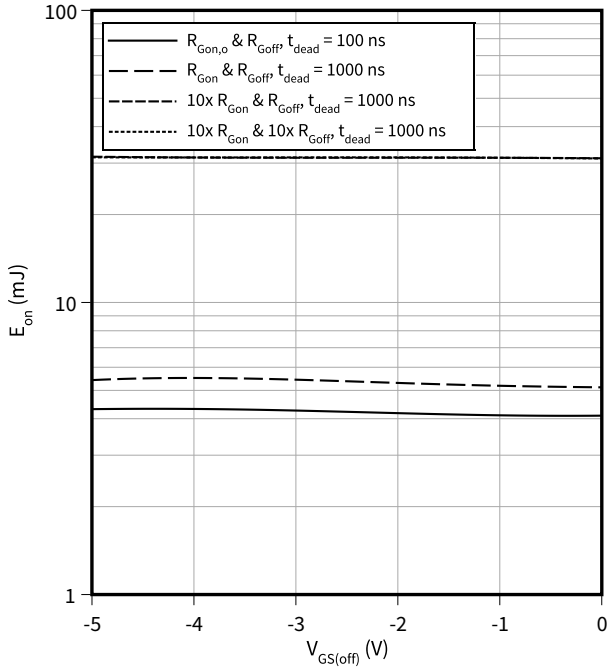
V_{DD} = 750 V, t_{dead} = 1000 ns, I_D = 120 A, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(V_{GS(off)})$

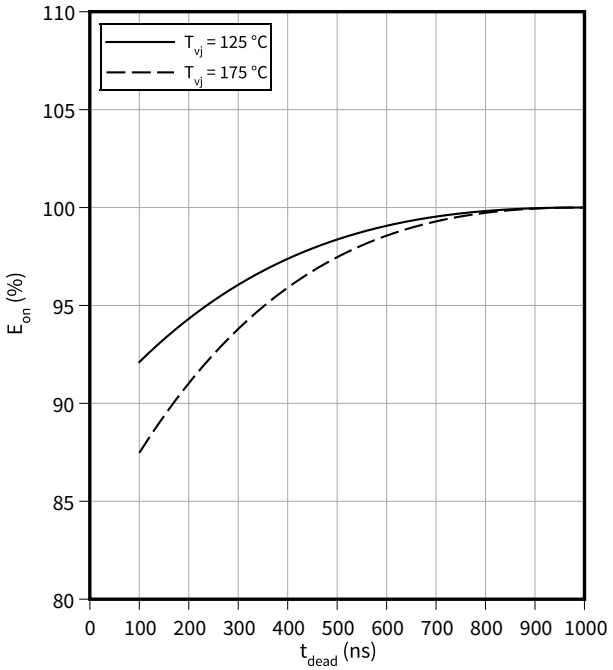
R_{Goff} = 0.25 Ω, V_{DD} = 750 V, R_{Gon} = 7.4 Ω, I_D = 120 A, $V_{GS(on)}$ = 18 V, $R_{Gon,o}$ = 6.8 Ω, T_{vj} = 175 °C



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(t_{dead})$

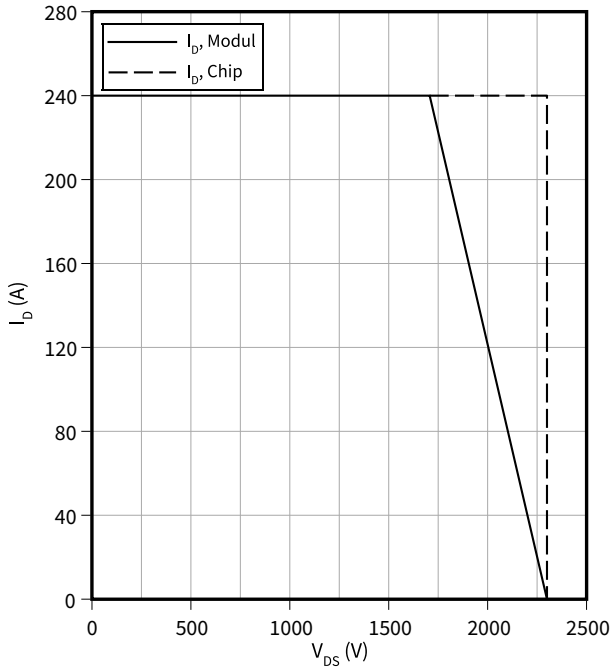
R_{Gon} = 7.4 Ω, V_{DS} = 750 V, I_D = 120 A, V_{GS} = -4/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

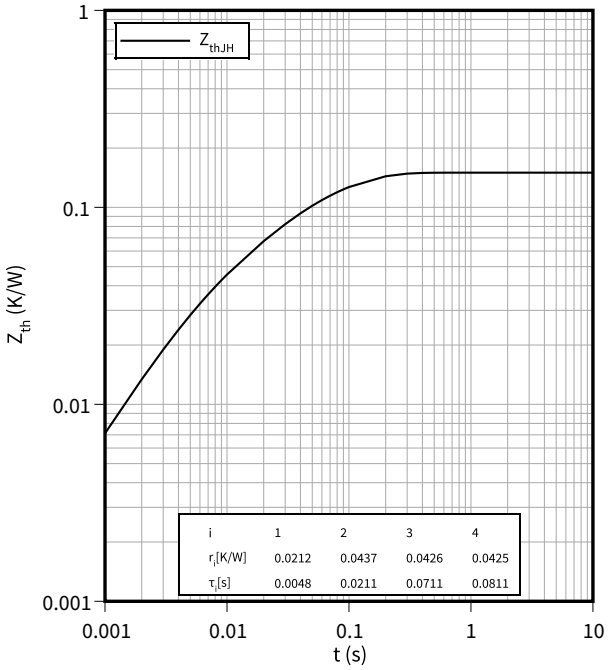
$I_D = f(V_{DS})$

R_{Goff} = 0.25 Ω, T_{vj} = 175 °C, V_{GS} = -4/18 V



Transient thermal impedance, MOSFET, T1 / T2

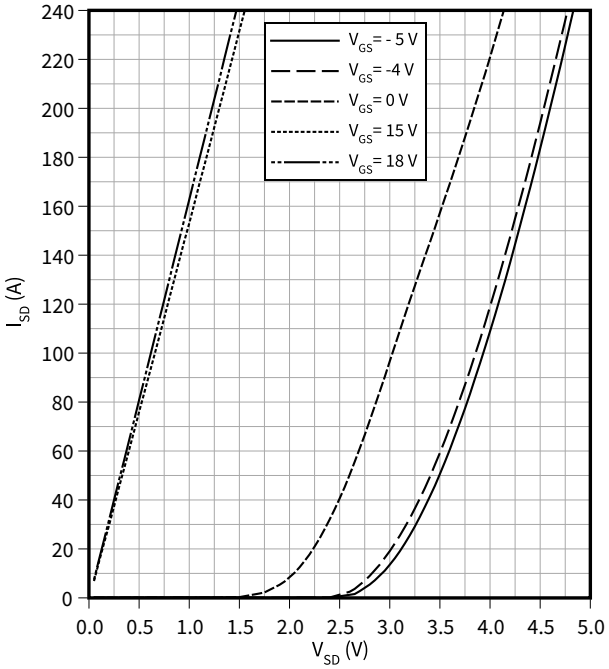
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T1 / T2

$I_{SD} = f(V_{SD})$

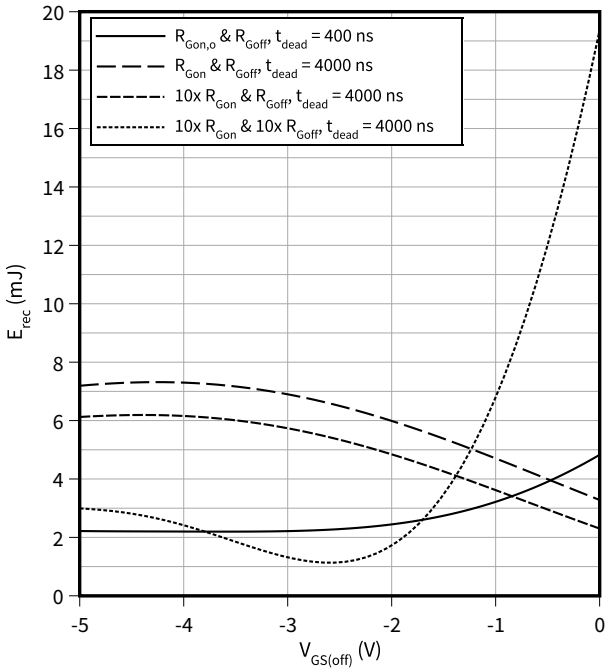
$T_{vj} = 25\ °C$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(V_{GS(off)})$

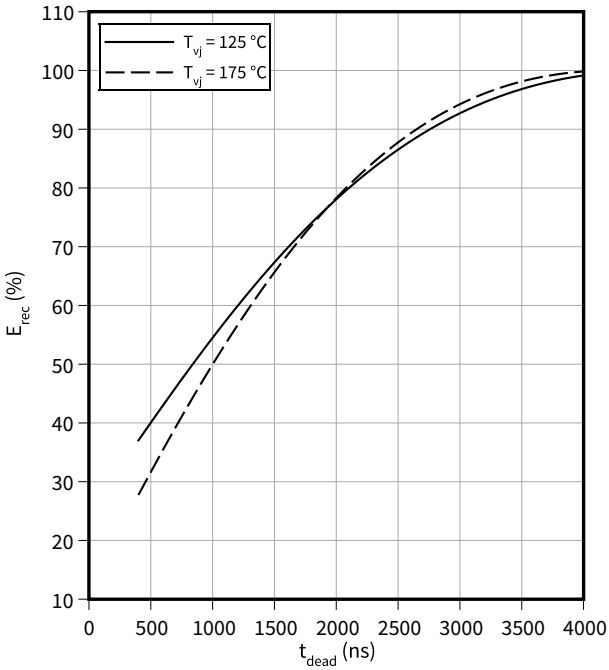
$R_{Goff} = 5.1\ \Omega$, $R_{Gon} = 0.25\ \Omega$, $V_{GS(on)} = 18\ V$, $I_{SD} = 120\ A$, $R_{Gon,o} = 0.25\ \Omega$, $V_{DD} = 750\ V$, $T_{vj} = 175\ °C$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(t_{dead})$

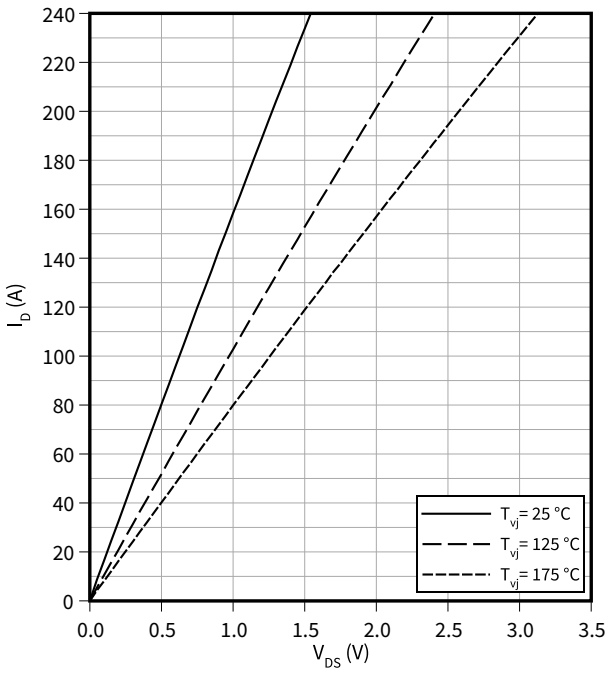
$R_{Gon} = 0.25\ \Omega$, $V_{DS} = 750\ V$, $I_D = 120\ A$, $V_{GS} = -4/18\ V$



Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$

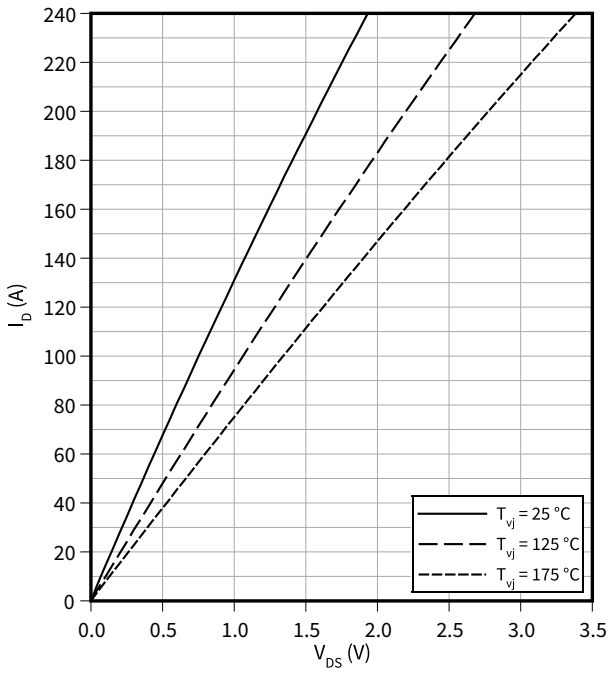
$V_{GS} = 18$ V



Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$

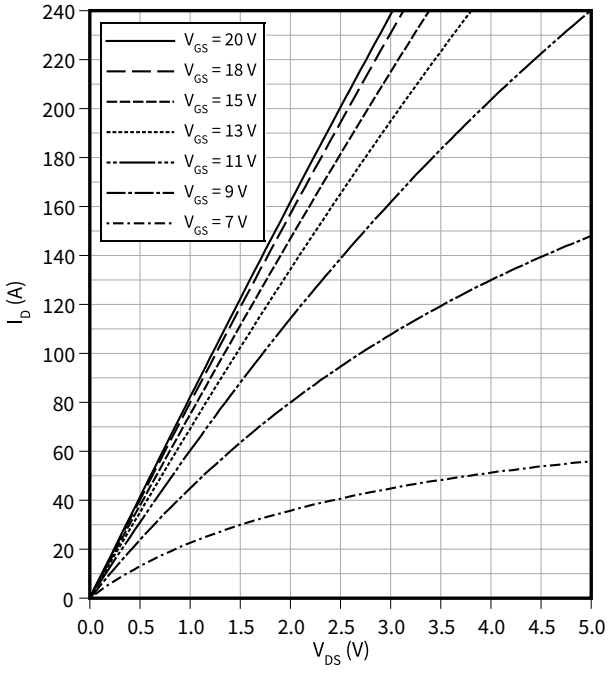
$V_{GS} = 15$ V



Output characteristic field (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$

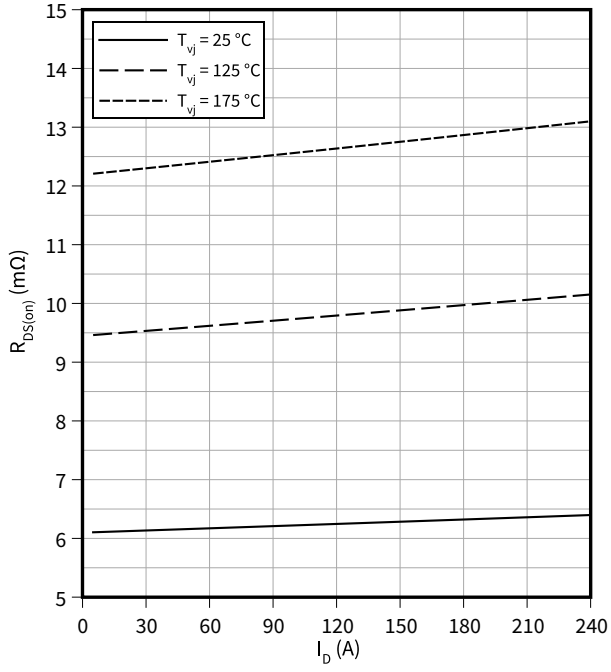
$T_{vj} = 175$ °C



Drain source on-resistance (typical), MOSFET, T3 / T4

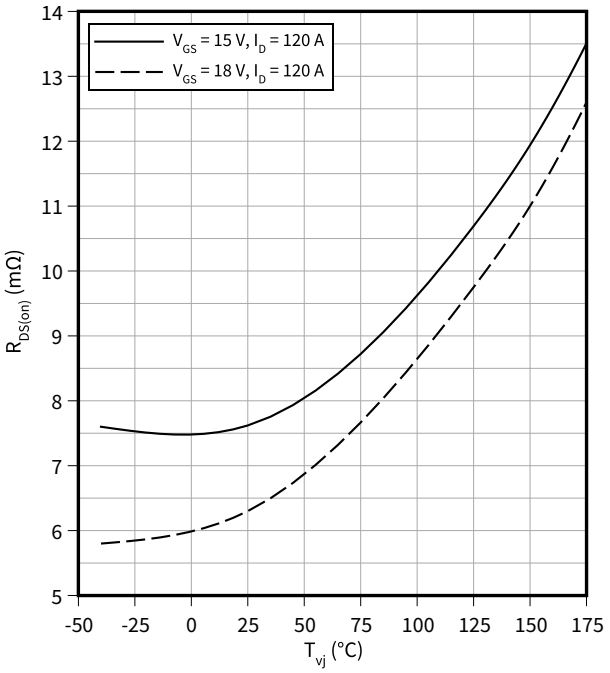
$R_{DS(on)} = f(I_D)$

$V_{GS} = 18$ V



Drain source on-resistance (typical), MOSFET, T3 / T4

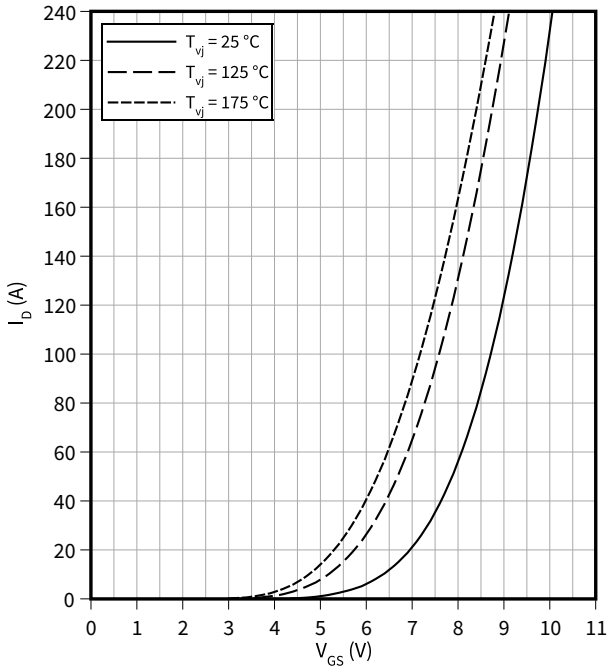
$R_{DS(on)} = f(T_{vj})$



Transfer characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{GS})$

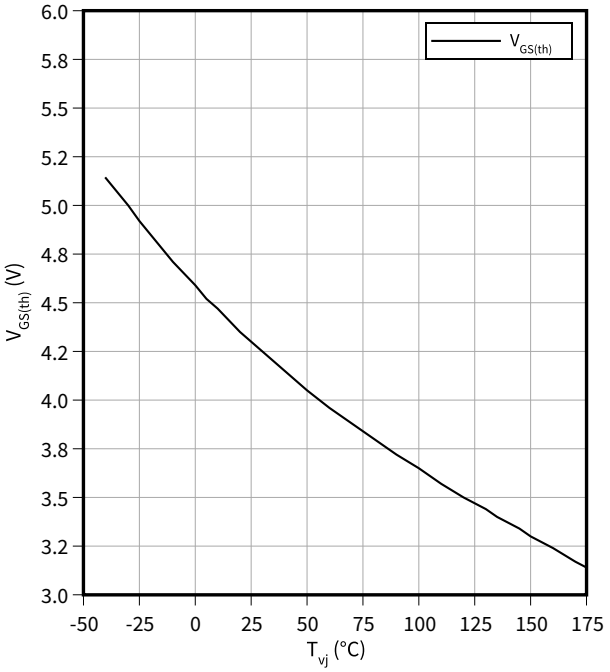
$V_{DS} = 20$ V



Gate-source threshold voltage (typical), MOSFET, T3 / T4

$V_{GS(th)} = f(T_{vj})$

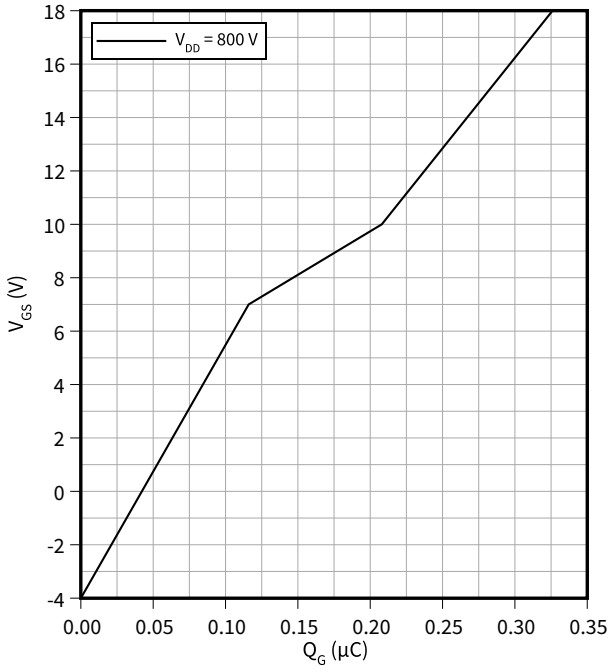
$I_D = 44$ mA, $V_{GS} = V_{DS}$



Gate charge characteristic (typical), MOSFET, T3 / T4

$V_{GS} = f(Q_G)$

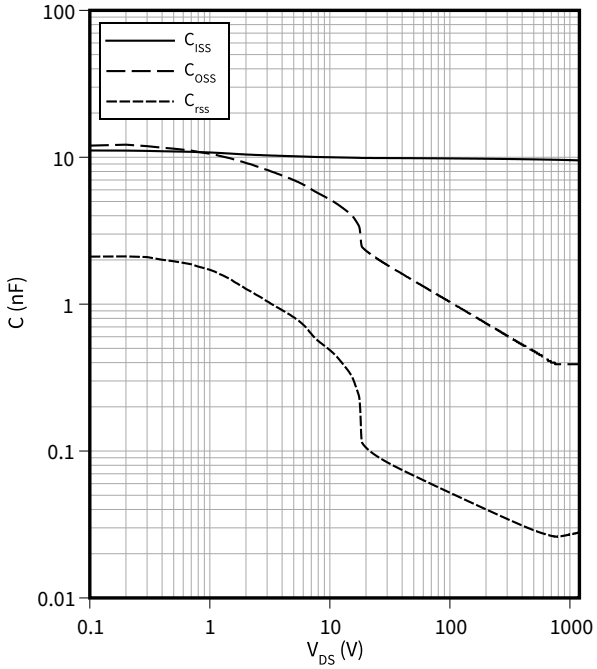
$I_D = 120$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET, T3 / T4

$C = f(V_{DS})$

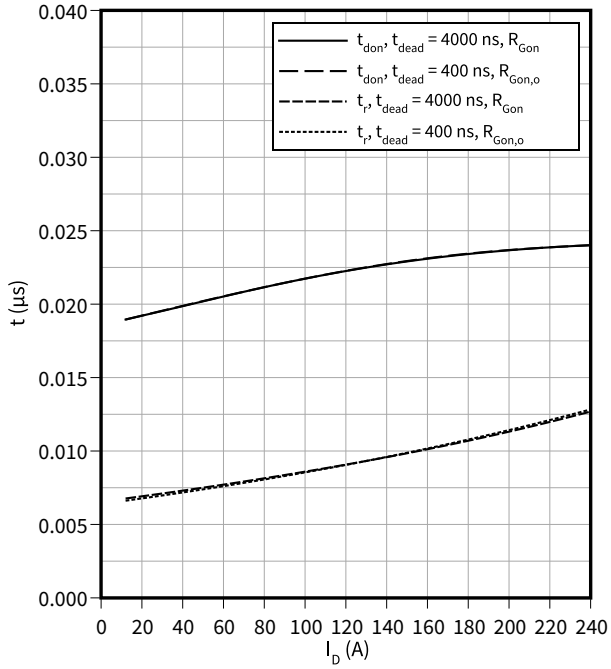
$f = 100$ kHz, $T_{vj} = 25$ °C, $V_{GS} = 0$ V



Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$

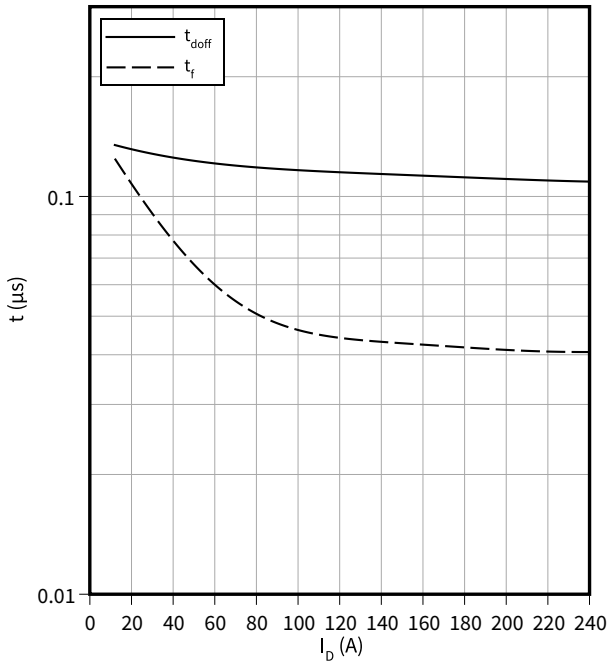
$R_{Gon} = 0.25\ \Omega$, $V_{DD} = 750$ V, $R_{Gon,o} = 0.25\ \Omega$, $T_{vj} = 175$ °C, $V_{GS} = -4/18$ V



Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$

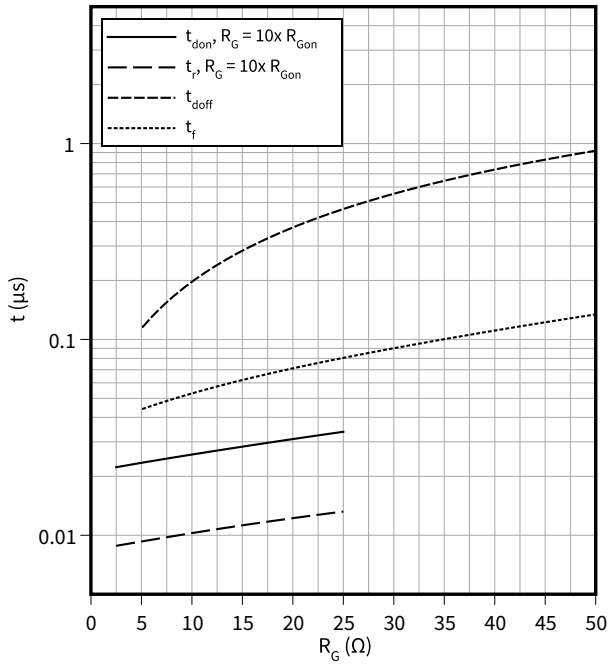
$R_{Goff} = 5.1\ \Omega$, $V_{DD} = 750$ V, $T_{vj} = 175$ °C, $V_{GS} = -4/18$ V



Switching times (typical), MOSFET, T3 / T4

$t = f(R_G)$

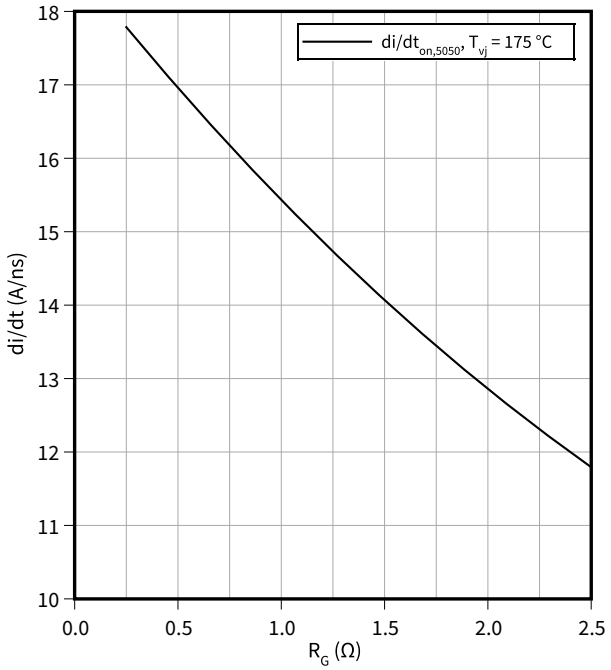
$V_{DD} = 750$ V, $t_{dead} = 4000$ ns, $I_D = 120$ A, $T_{vj} = 175$ °C, $V_{GS} = -4/18$ V



Current slope (typical), MOSFET, T3 / T4

$di/dt_{on} = f(R_G)$

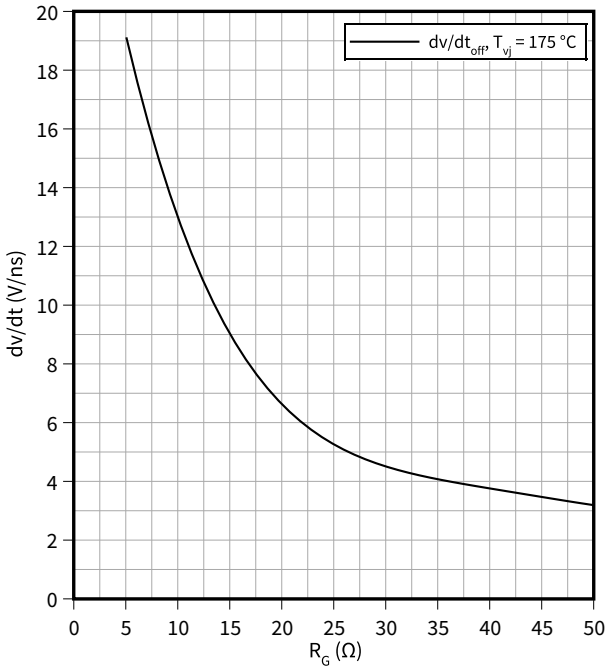
V_{DD} = 750 V, t_{dead} = 4000 ns, I_D = 120 A, V_{GS} = -4/18 V



Voltage slope (typical), MOSFET, T3 / T4

$dv/dt_{off} = f(R_G)$

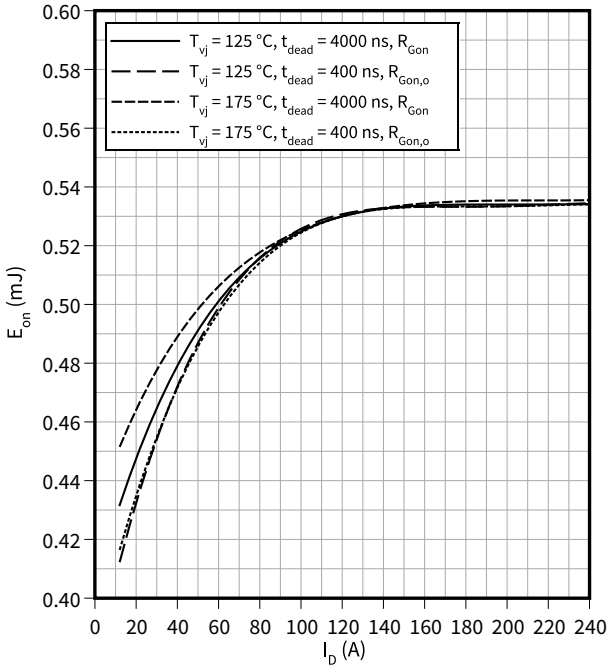
V_{DD} = 750 V, I_D = 120 A, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(I_D)$

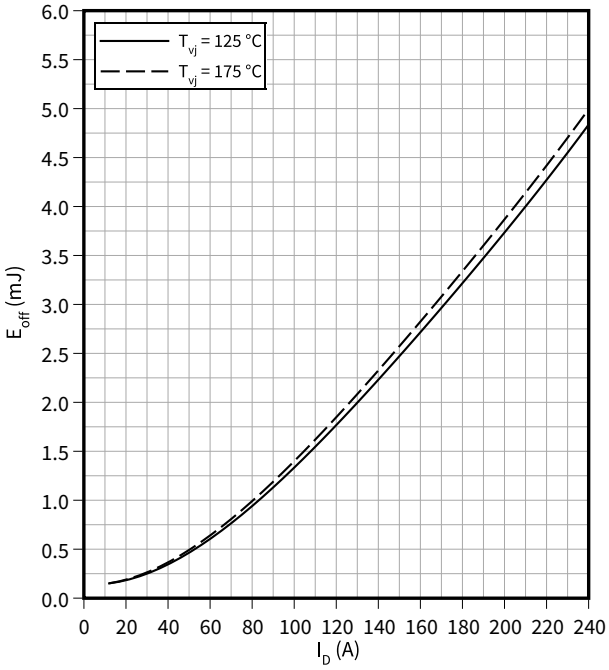
V_{DD} = 750 V, R_{Gon} = 0.25 Ω, $R_{Gon,o}$ = 0.25 Ω, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{off} = f(I_D)$

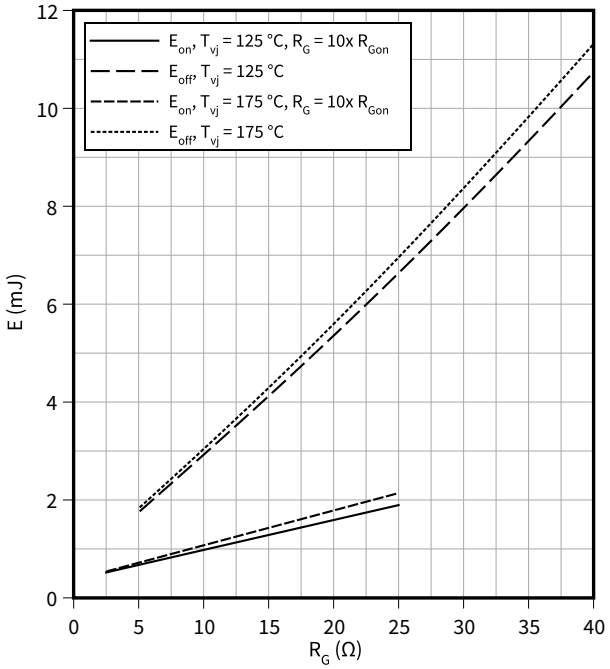
R_{Goff} = 5.1 Ω, V_{DD} = 750 V, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T3 / T4

$E = f(R_G)$

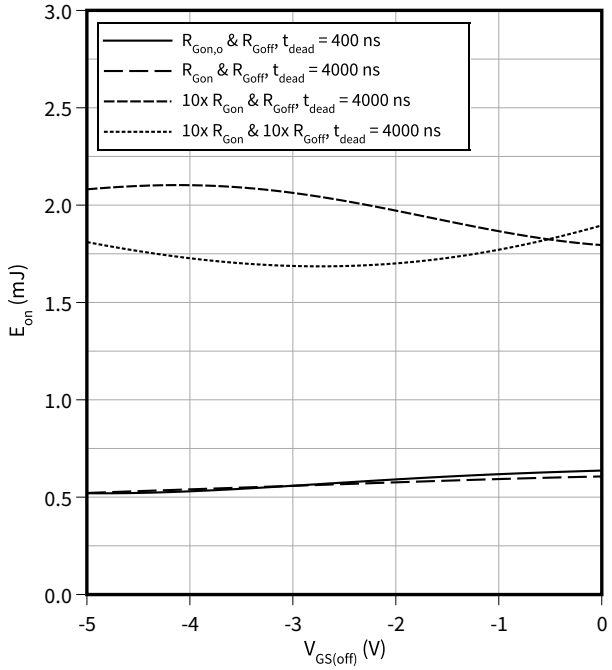
V_{DD} = 750 V, t_{dead} = 4000 ns, I_D = 120 A, V_{GS} = -4/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(V_{GS(off)})$

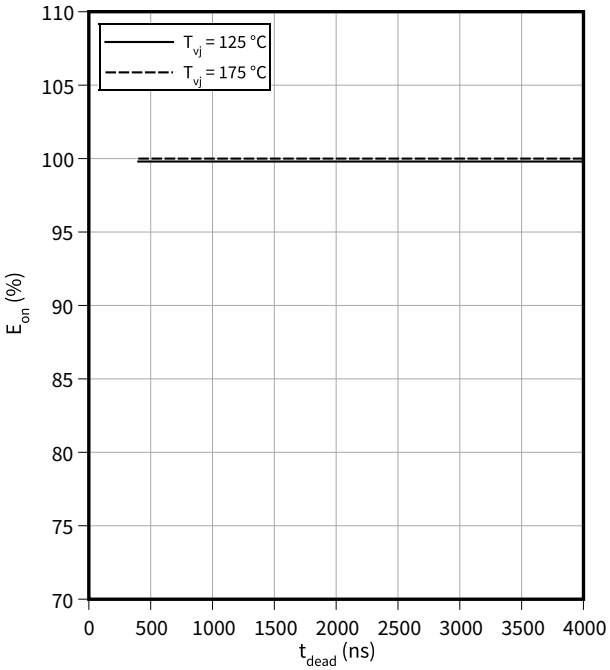
R_{Goff} = 5.1 Ω, V_{DD} = 750 V, R_{Gon} = 0.25 Ω, $V_{GS(on)}$ = 18 V, I_D = 120 A, $R_{Gon,o}$ = 0.25 Ω, T_{vj} = 175 °C



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(t_{dead})$

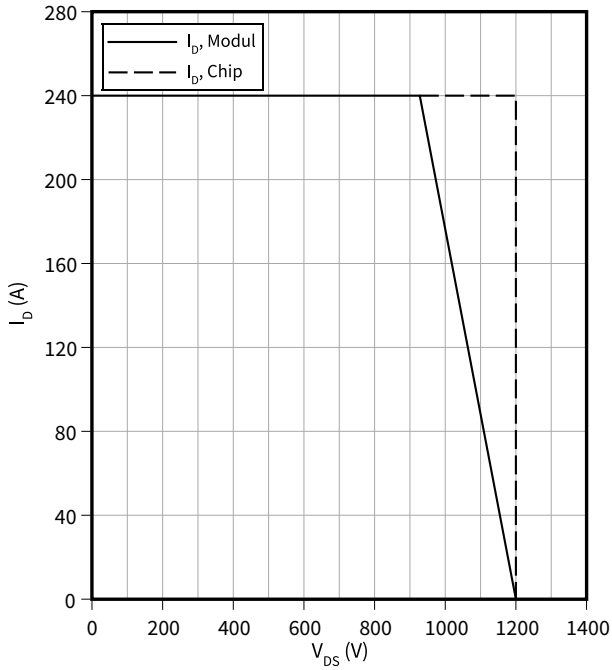
R_{Gon} = 0.25 Ω, I_D = 120 A, V_{DD} = 750 V, V_{GS} = -4/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T3 / T4

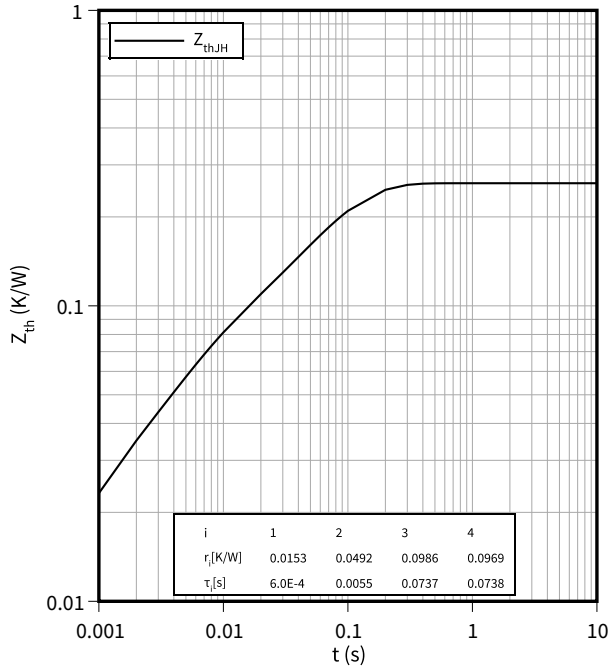
$I_D = f(V_{DS})$

R_{Goff} = 5.1 Ω, T_{vj} = 175 °C, V_{GS} = -4/18 V



Transient thermal impedance, MOSFET, T3 / T4

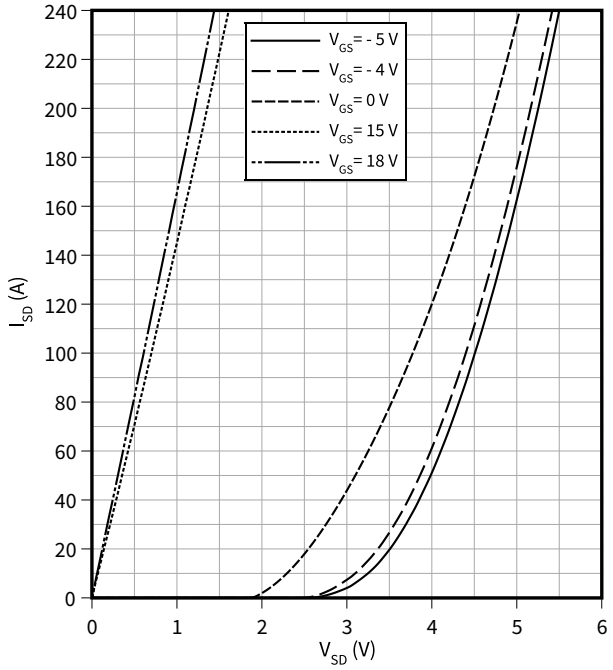
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T3 / T4

$I_{SD} = f(V_{SD})$

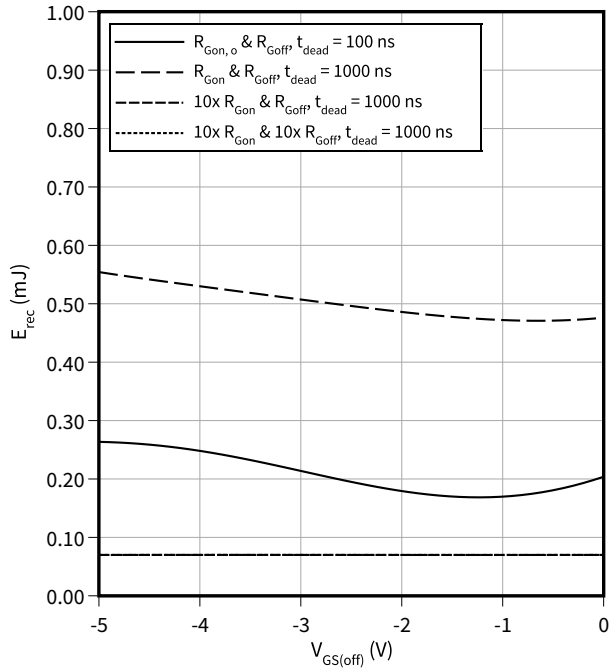
$T_{vj} = 25\ °C$



Switching losses body diode (typical), MOSFET, T3 / T4

$E_{rec} = f(V_{GS(off)})$

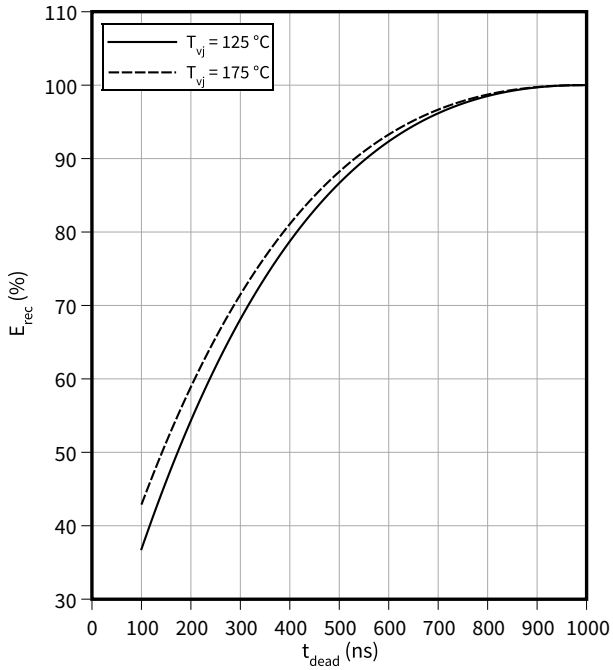
$R_{Goff} = 0.25\ \Omega$, $R_{Gon} = 7.4\ \Omega$, $V_{GS(on)} = 18\ V$, $I_{SD} = 120\ A$, $R_{Gon,o} = 6.8\ \Omega$, $V_{DD} = 750\ V$, $T_{vj} = 175\ °C$



Switching losses body diode (typical), MOSFET, T3 / T4

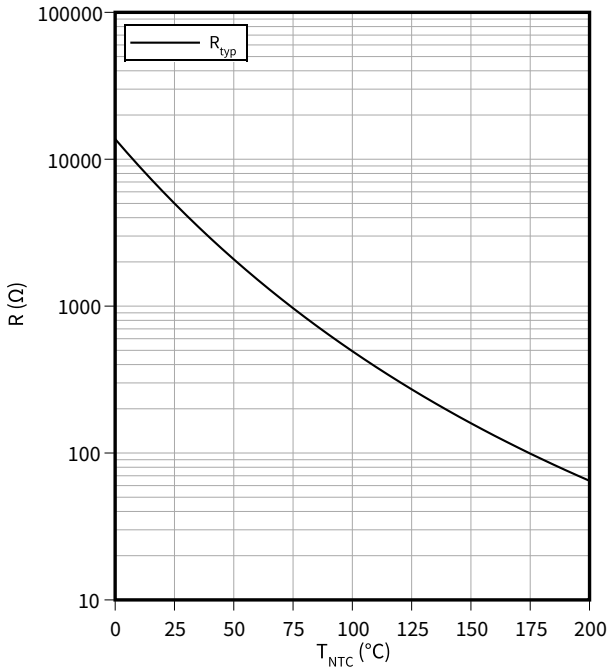
$E_{rec} = f(t_{dead})$

$R_{Gon} = 7.4\ \Omega$, $I_D = 120\ A$, $V_{DD} = 750\ V$, $V_{GS} = -4/18\ V$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



8 Circuit diagram

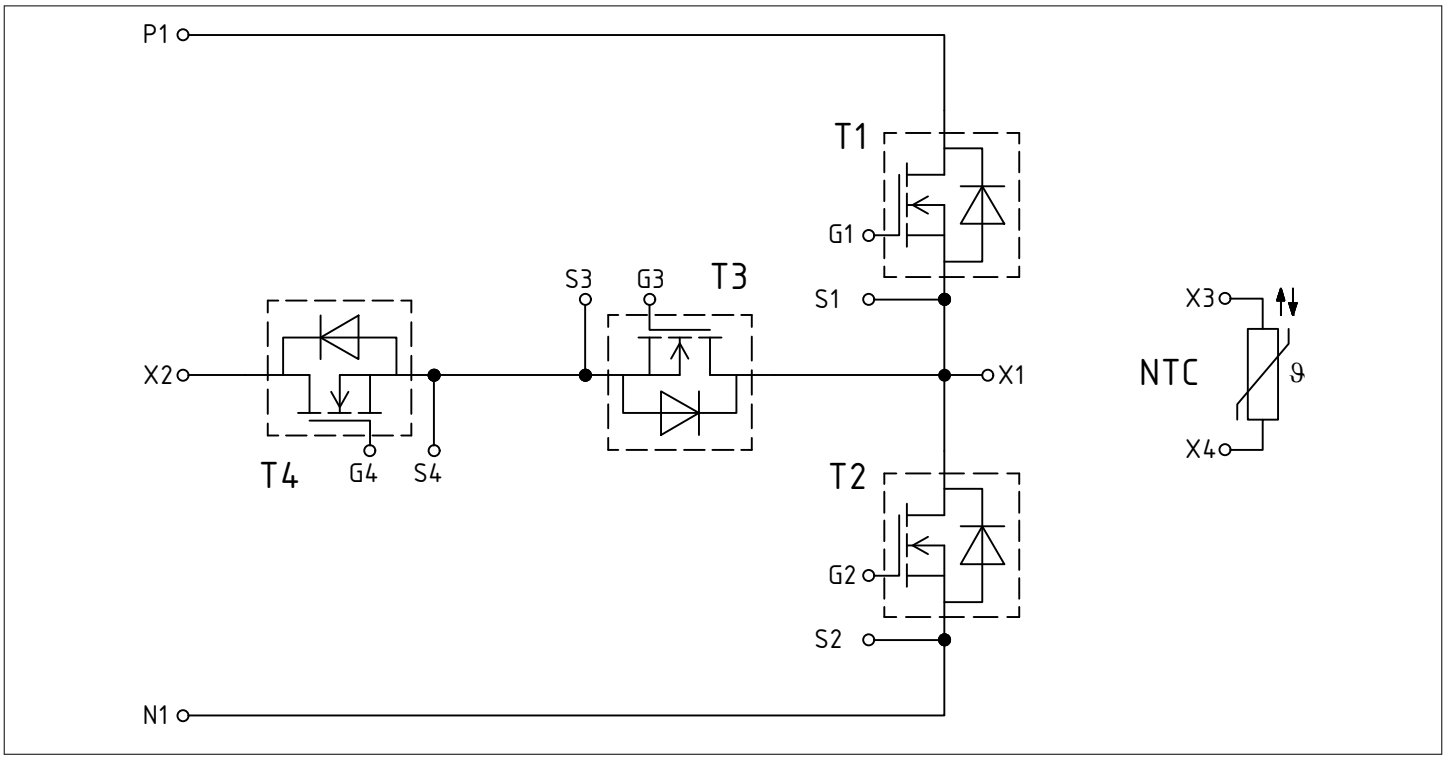


Figure 1

9 Package outlines

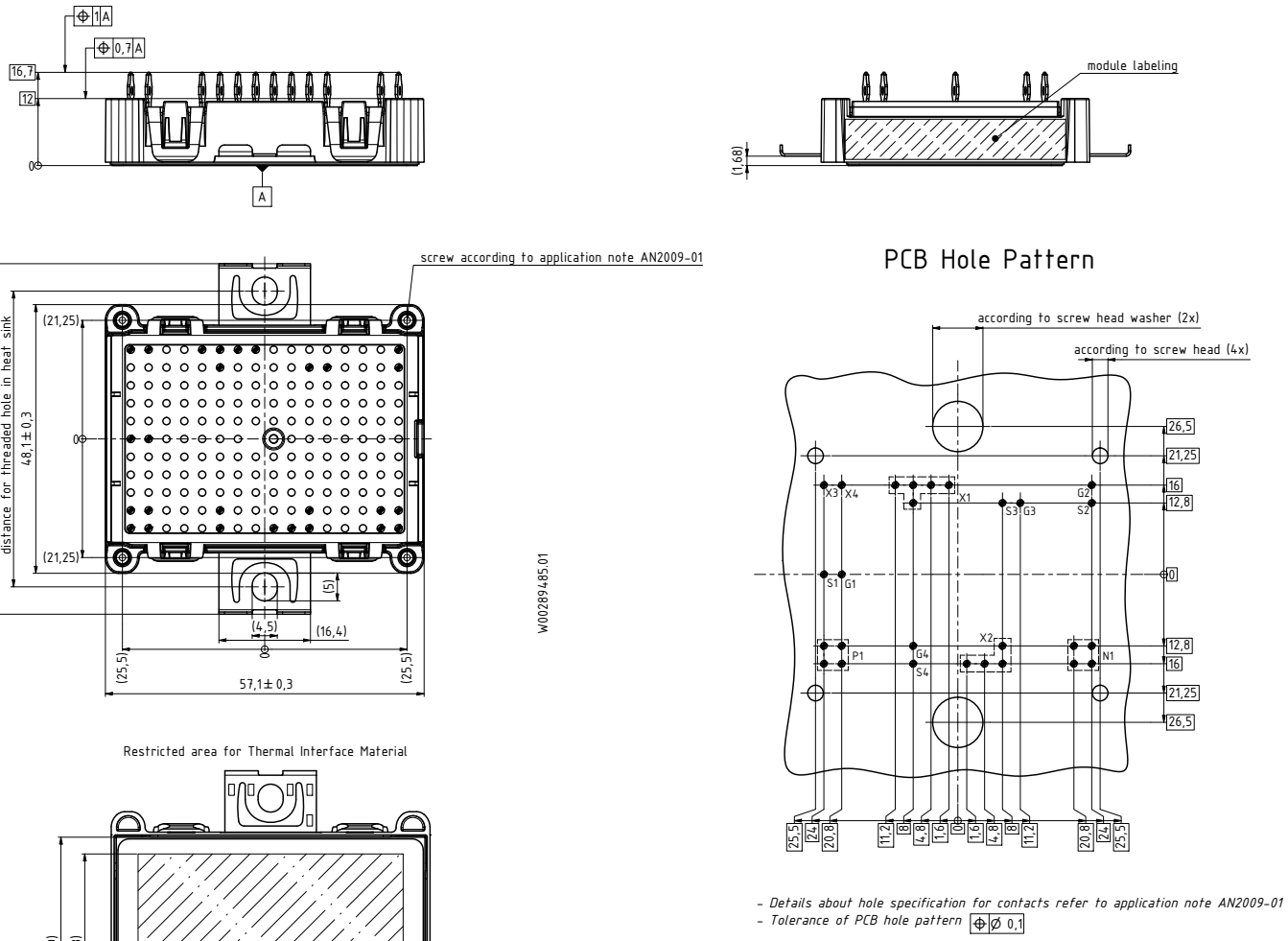


Figure 2

10 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	7154914284655054991530		7154914284655054991530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2025-05-16	Target datasheet
0.20	2026-05-29	Preliminary datasheet

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